

PNP Germanium Transistors

**AC 121
AC 152**

SIEMENS AKTIENGESELLSCHAFT

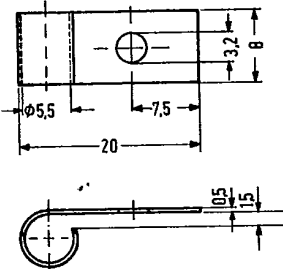
for AF, driver and output stages of medium performance

AC 121 and AC 152 are alloyed germanium PNP transistors in 1 A 3 DIN 41871 metal case (similar to TO 1).

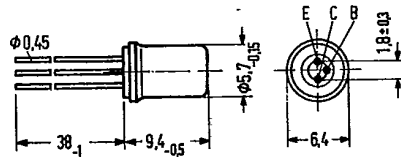
The leads of these transistors are electrically insulated from the case. The collector terminal is marked by a red dot at the rim of the case. For use in push-pull output stages, the transistors AC 121 and AC 152 are available in pairs. A fixing part (heat sink¹⁾) is provided for fixing on the chassis; it has to be ordered separately.

Not for new design

Type	Ordering code	Type	Ordering code
AC 121 IV	Q60103-D121	AC 152 IV	Q60103-X152-D
AC 121 V	Q60103-E121	AC 152 V	Q60103-X152-E
AC 121 VI	Q60103-F121	AC 152 VI	Q60103-X152-F
AC 121 VII	Q60103-G121	AC 152 paired	Q60103-X152-P
AC 121 paired	Q60103-P121-X1	Heat sink	Q62901-B1



Approx. weight 2 g



Approx. weight 1 g

Dimensions in mm

Maximum ratings

	AC 121	AC 152		
Collector-emitter voltage	-V _{CEO}	20	24	V
Collector-emitter voltage (V _{BE} ≥ 0.2 V)	-V _{CEV}	20	32	V
Collector-base voltage	-V _{CBO}	20	32	V
Emitter-base voltage	-V _{EBO}	10	10	V
Collector current	-I _C	300	500	mA
Base current	-I _B	60	100	mA
Junction temperature	T _J	90	90	°C
Storage temperature range	T _{stg}	-55 to +75		°C
Total power dissipation	P _{tot}	900	900	mW

Thermal resistance

	R _{thJA}	R _{thJC}	
Junction to ambient air	≤300	≤300	K/W
Junction to case	≤50	≤50	K/W

¹⁾ Thermal resistance between transistor case and heat sink below the fixing screw at careful mounting: R_{th} ≤ 10 K/W

Static characteristics ($T_{amb} = 25^{\circ}\text{C}$)

The transistors AC 121, AC 152 are grouped according to the DC current gain h_{FE} at $-I_C = 100\text{ mA}$, and marked by the Roman numerals. The following values apply at a collector voltage of $-V_{CE} = 0.5\text{ V}$ and the following collector currents:

h_{FE} group		IV	V	VI	VII	
		AC 152	AC 152	AC 152	-	AC 152
Type		AC 121	AC 121	AC 121	AC 121	AC 121
$-I_C$ mA	$-I_C$ mA	h_{FE} I_C/I_B	h_{FE} I_C/I_B	h_{FE} I_C/I_B	h_{FE} I_C/I_B	$-V_{BE}$ V
[2]	3	48 [47]	80 [78]	115 [114]	200	0.13 (<0.22)
100	100	45 (30 to 60)	75 (50 to 100)	110 (75 to 150)	190 (125 to 250)	0.32 (<0.55)
[500]	300	35 [28]	58 [47]	86 [68]	148	0.44 (<0.8) [0.52 (<1.0)]

Static characteristics ($T_{amb} = 25^{\circ}\text{C}$)

Collector-emitter saturation voltage
 ($-I_C = 100\text{ mA}$; $h_{FE} = 20$)
 Collector-emitter saturation voltage
 ($-I_C = 300\text{ mA}$; $h_{FE} = 20$)
 Collector-emitter saturation voltage
 Emitter cutoff current ($-V_{EBO} = 10\text{ V}$)
 Collector cutoff current ($-V_{CBO} = 20\text{ V}$)
 Collector cutoff current
 ($-V_{CEV} = 20\text{ V}$; $V_{BE} \geq 0.2\text{ V}$)

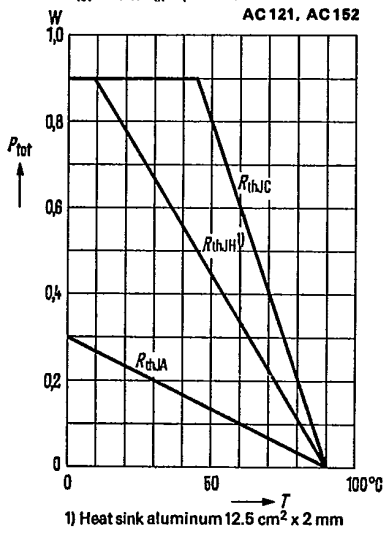
	AC 121	
$-V_{CEsat}^{1)}$	0.11 (<0.3)	V
$-V_{CEsat}^{1)}$	0.15 (<0.35)	V
$-V_{CEsat}$	0.28 (<0.45) ²⁾	V
$-I_{EBO}$	4 (<25)	μA
$-I_{CBO}$	5 (<25)	μA
$-I_{CEV}$	5 (<25)	μA

Collector-emitter saturation voltage
 ($-I_C = 100\text{ mA}$; $h_{FE} = 20$)
 Collector-emitter saturation voltage
 ($-I_C = 300\text{ mA}$; $h_{FE} = 20$)
 Collector-emitter saturation voltage
 Collector cutoff current ($-V_{CBO} = 32\text{ V}$)
 Collector cutoff current ($-V_{CEV} = 32\text{ V}$;
 $V_{BE} = 0.2\text{ V}$)
 Emitter cutoff current ($V_{EBO} = 10\text{ V}$)

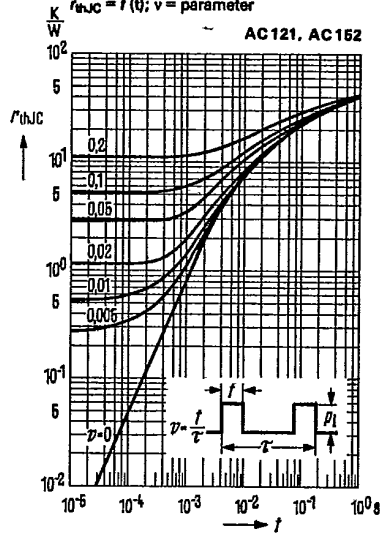
	AC 152	
$-V_{CEsat}^{1)}$	0.11 (<0.18)	V
$-V_{CEsat}^{1)}$	0.15 (<0.25)	V
$-V_{CEsat}$	0.32 (<0.5) ²⁾	V
$-I_{CBO}$	6 (<25)	μA
$-I_{CEV}$	6 (<25)	μA
$-I_{EBO}$	4 (<25)	μA

1) The transistor is overloaded to such a degree that the DC current gain decreases to $h_{FE} = 20$.
 2) ($-I_C = 500\text{ mA}$ for the characteristic which, at a constant base current, intersects the operating point, where $-I_C = 550\text{ mA}$; $-V_{CE} = 0.5\text{ V}$)

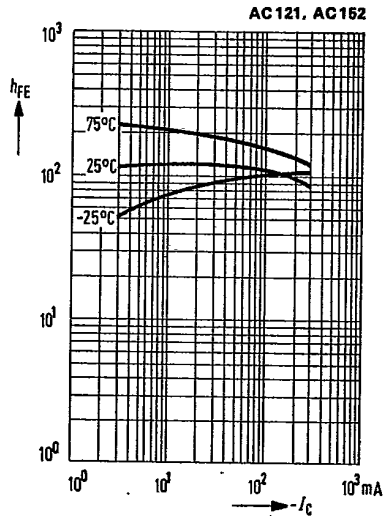
Total perm. power dissipation versus temperature
 $P_{tot} = f(T); R_{th} = \text{parameter}$



Permissible pulse load
 $r_{thJC} = f(t); v = \text{parameter}$

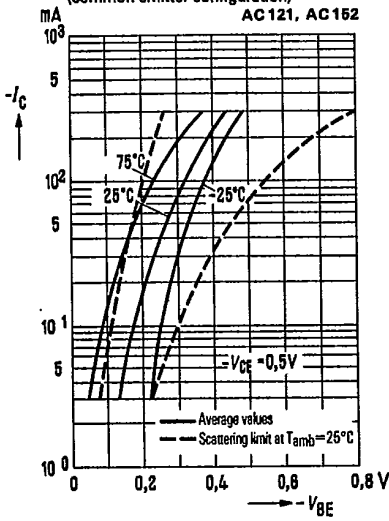


DC current gain $h_{FE} = f(I_C)$
- $V_{CE} = 0.5 \text{ V}; T_{amb} = \text{parameter}$
(common emitter configuration)



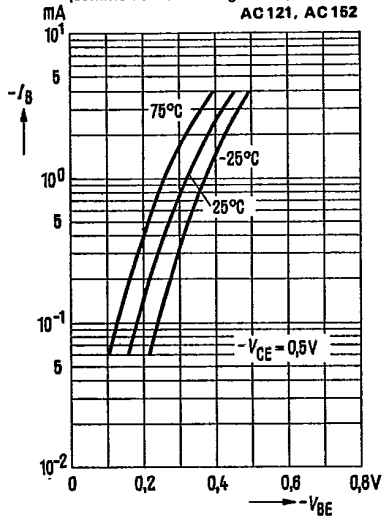
Collector current $I_C = f(V_{BE})$
 $-V_{CE} = 0.5\text{ V}; T_{amb} = \text{parameter}$
 (common emitter configuration)

AC 121, AC 152



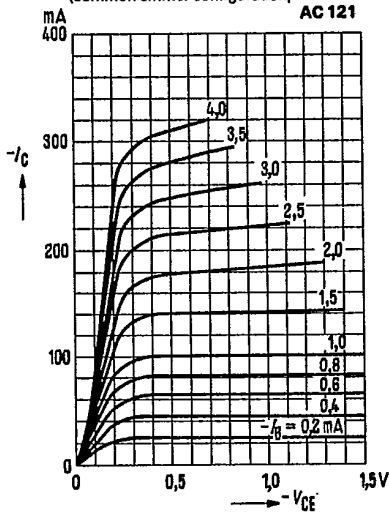
Input characteristics $I_B = f(V_{BE})$
 $-V_{CE} = 0.5\text{ V}; T_{amb} = \text{parameter}$
 (common emitter configuration)

AC 121, AC 152



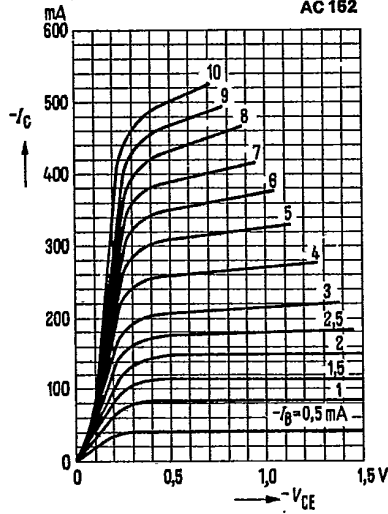
Output characteristics
 $I_C = f(V_{CE}); I_B = \text{parameter}$
 (common emitter configuration)

AC 121



Output characteristics
 $I_C = f(V_{CE}); I_B = \text{parameter}$
 (common emitter configuration)

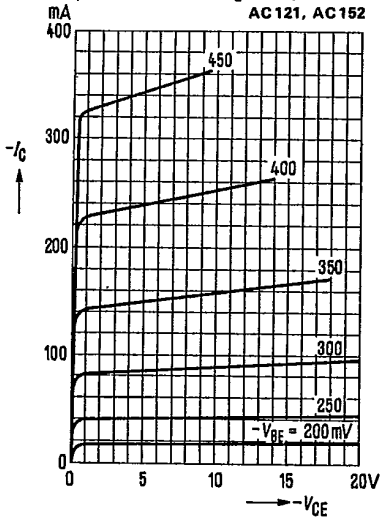
AC 152



T-29-11

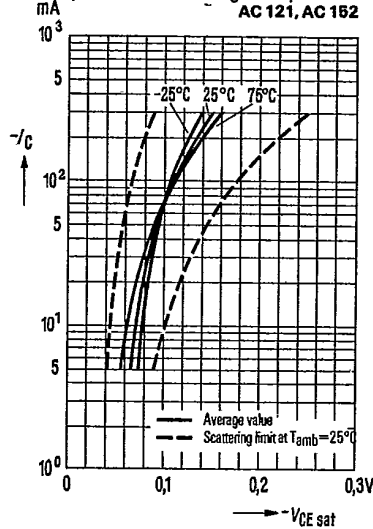
Output characteristics
 $I_C = f(V_{CE}); V_{BE} = \text{parameter}$
(common emitter configuration)

AC 121, AC 152



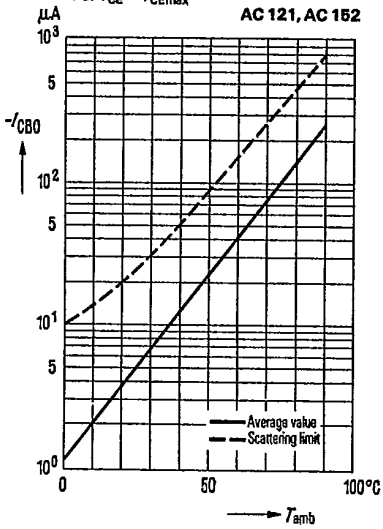
Collector emitter saturation voltage
 $V_{CEsat} = f(I_C); h_{FE} = 20$
(common emitter configuration)

AC 121, AC 152



Collector cutoff current versus temperature
 $I_{CBO} = f(T_{amb})$
For $V_{CE} = V_{CEmax}$

AC 121, AC 152



Collector-emitter voltage
 $V_{CER} = f(R_{BE})$

AC 152

